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Chiral Symmetry and Electron Spin Relaxation of Lithium Donors in Silicon

V. N. Smelyanskiy,[1,*] A. G. Petukhov,[2,†] A. M. Tyryshkin,[3]
S. A. Lyon,[3] T. Schenkel,[4] J. W. Ager,[4] and E. E. Haller[4]

[1]*NASA Ames Research Center, Mail Stop 269-3, Moffett Field, CA 94035, USA*
[2]*Department of Physics, South Dakota School of*
Mines and Technology, Rapid City, SD 57701, USA
[3]*Department of Electrical Engineering,*
Princeton University, Princeton, NJ 08544, USA
[4]*Lawrence Berkeley National Laboratory, Berkeley, CA 94720, USA*

Abstract

We report theoretical and experimental studies of the longitudinal electron spin and orbital relaxation time of interstitial Li donors in ^{28}Si. We predict that despite the near-degeneracy of the ground-state manifold the spin relaxation times are extremely long for the temperatures below 0.3 K. This prediction is based on a new finding of the chiral symmetry of the donor states, which presists in the presence of random strains and magnetic fields parallel to one of the cubic axes. Experimentally observed kinetics of magnetization reversal at 2.1 K and 4.5 K are in a very close agreement with the theory. To explain these kinetics we introduced a new mechanism of spin decoherence based on a combination of a small off-site displacement of the Li atom and an umklapp phonon process. Both these factors weakly break chiral symmetry and enable the long-term spin relaxation.

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I. INTORDUCTION

Recent progress in building devices for quantum information processing (QIP) has lead to renewed interest in studying the relaxation times of electron spins bound to impurities and in quantum dots to be used for encoding quantum information[1,2,3,4,5]. Electron spins bound to shallow donors in Si are characterized by particularly long relaxation times, since the spin orbit interaction is weak and isotopically enriched ^{28}Si is available[6,7]. However a weak interdonor spin coupling represents a challenge for the controlled interaction of quantum bits.

The interstitial lithium donor in silicon is unique amongst shallow donors because it has an inverted level structure and near degeneracy of the $1s$ ground state manifold[8,9]. The latter gives rise to a strong long-range elastic-dipole coupling of the neutral Li donor *orbital* states[10], similar to that obtained earlier for acceptors in Si[11] but absent in the case of other donors. In[10] a quantum computing architecture was proposed based on the stress-defined orbital qubits and the above interaction was used to enable 2-qubit gates. At the same time the near degeneracy of $1s$ manifold in Si:Li also gives rise to a nontrivial coupling between the spin and orbital degrees of freedom first investigated by Watkins and Ham[12]. One can expect that the inverted level structure and near degeneracy in Si:Li will lead to a very short electron spin relaxation times which can also strongly affect orbital relaxation and be detrimental for QIP. Somewhat surprisingly, in view of extensive studies of spin relaxation of other shallow donors in silicon since the early sixties, both experimental[6,7,13,14] and theoretical[15,16], the question about Li spin relaxation has not been addressed.

In this work we propose a new relaxation mechanism for coupled donor electron spin and orbital degrees of freedom. It is based on (i) our new finding of the chiral symmetry of the donor states that persists in prsence of the random starin and magnetic field of certain orientations and (ii) an interplay between the umklapp phonon processes and a short-range electric dipole interaction that only weakly break this symmetry and enable spin relaxation. As a result Li electron spin and orbital relaxation times become very long in the presence of modest external stress ($\sim 10^7$ Pa) at temperatures below 0.3 K. We also report pulsed ESR measurements of the longitudinal spin relaxation time T_1 in ^{28}Si:Li at temperatures 1.8 to 4.5 K. We find that in the absence of external stress these times are shorter than our instrumental resolution (< 100 ns) at temperatures as low as 1.8 K. This rapid relaxation is caused by the degeneracy in the ground state manifold. However, a modest applied stress lifts the degeneracy, and leads to a much longer relaxation, as will be discussed below. The results of the theoretical analysis of the selection rules and spin-orbital relaxation mechanisms are in excellent quantitative agrement with the experiment as shown in Fig 1.

The ground state $1s$ manifold of an interstitial lithium donor in silicon can be described by the Hamiltonian in a twelve dimensional Hilbert space formed by a tensor product of electron spin states $|\chi_\pm\rangle$ and six $1s$ orbitals corresponding to the six conduction band minima $\mathbf{k}_i$[12]

$$H = H^{(0)} + H_{\rm d}, \quad H^{(0)} = H_{\rm o} + H_{\rm B} + H_{\rm st} + H_{\rm so}. \tag{1}$$

The term $H_{\rm o}$ is the spin-diagonal, effective mass orbital $1s$ Hamiltonian also describing the valley-orbit splitting due to the short range tetrahedral potential. The rest of individual terms in H to be considered below describe the coupling of the donor electron to magnetic field ($H_{\rm B}$), long-wavelength strain field ($H_{\rm st}$) , spin-orbit interaction ($H_{\rm so}$), and a small off-center displacement of Li core from the symmetry site ($H_{\rm d}$).

For each of the two spin orientations the six eigenstates of $H_{\rm o}$ are linear superpositions of the six silicon valley orbitals, $\psi_\mu(\mathbf{r}) = \sum_{j=\pm 1}^{\pm 3} \alpha_j^\mu F_j(\mathbf{r}) u_j(\mathbf{r})$. Here $F_j(\mathbf{r})$ and $u_j(\mathbf{r})$ are, respectively, the hydrogenic envelope and the Bloch function for the j-th conduction band minima $\mathbf{k}_j = k_0 \hat{x}_j$ ($\hat{x}_j{=}\pm\hat{x}, \pm\hat{y}$ or $\pm\hat{z}$). Eigenstate $\psi_\mu(\mathbf{r})$ belongs to the irreducible representation μ of the tetrahedral group characterized by the valley-orbit coefficients α_j^μ. In contrast to the Group V substitutional donors the ground state of $H_{\rm o}$ is five-fold degenerate for each spin orientation. It is composed of a triplet of states T_{2x}, T_{2y}, T_{2z} which are anti-symmetric combinations of just two opposite valleys, $\alpha_j^\mu = -\alpha_{-j}^\mu$, and a doublet E_θ, E_ϵ that are symmetric combinations of valleys, $\alpha_j^\mu = \alpha_{-j}^\mu$, with a second-order zero at the origin. A fully symmetric singlet state A_1 lies at $\Delta_0{=}$ 1.76 meV above the $1s(E+T_2)$ orbital ground state[8,9], so that matrix elements $\langle\psi_\mu|H_{\rm o}|\psi_{\mu'}\rangle = \Delta_0 \delta_{\mu,A_1}\delta_{\mu',A_1}\hat{I}$, where $\hat{I}$ is $2{\times}2$ unit matrix operating in spin subspace.

II. PARITY-SELECTION RULES FOR ACOUSTIC-PHONON TRANSITIONS

Electron-phonon interaction $H_{\mathbf{q}\nu}$ within $1s(E{+}T_2)$ manifold can be described in terms of deformation potentials because the states there decay via emission of long-wavelength acoustic phonons with $q{\sim}10^5\text{cm}^{-1}$. A matrix element between a pair of donor states ψ_μ and

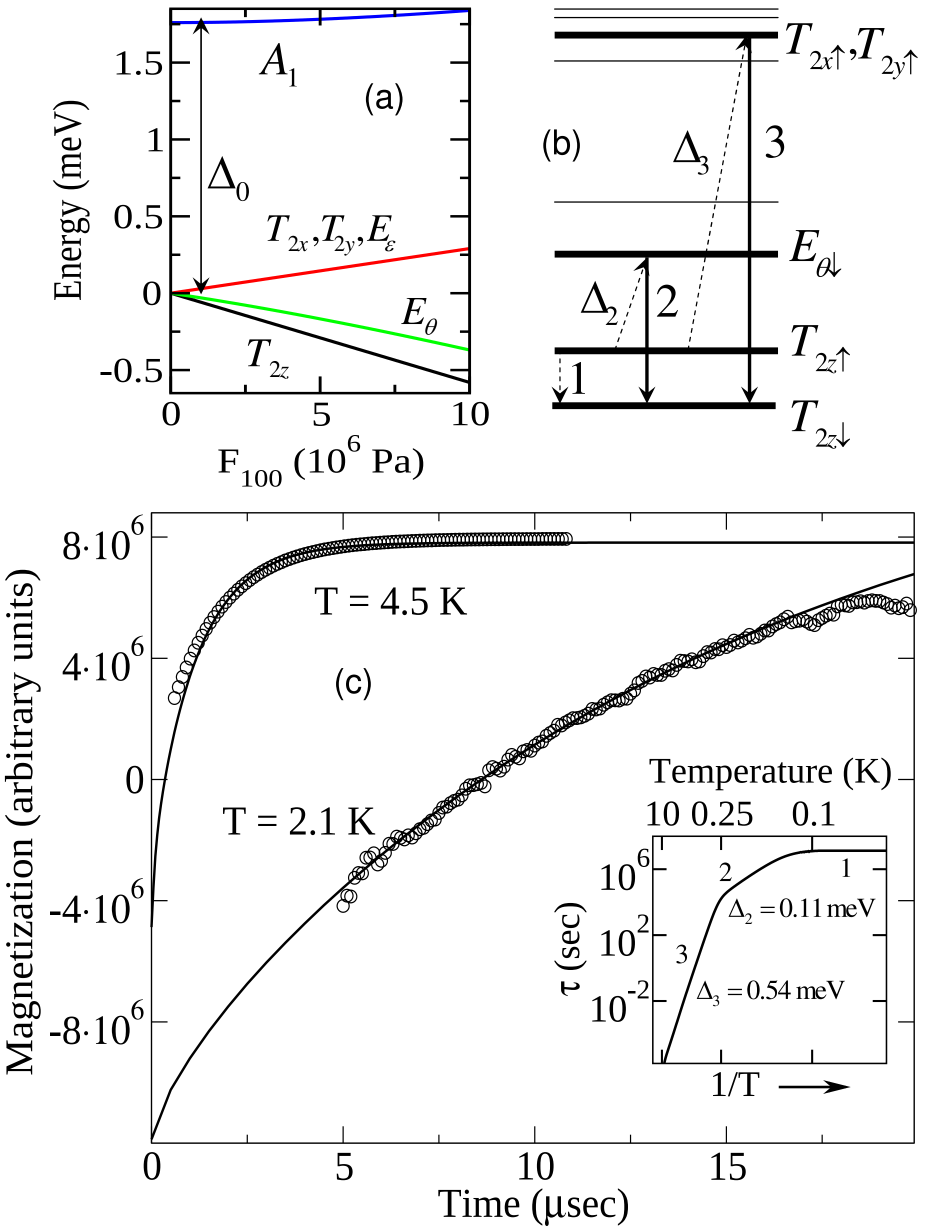

FIG. 1: (a) Theoretical stress dependence of Si:Li $1s$ energy levels at $B = 0$. (b) Energy levels at finite stress and $B \neq 0$. Solid lines 2,3 indicate the relatively fast one-phonon transitions connecting the states with the *same* chirality. Dashed line 1 indicates the slow spin-flip transition between the "left" and "right" states; (c) Comparison of experimental and theoretical kinetics of magnetization recovery at 2.1 K and 4.5 K. The theoretical curves (thin solid lines) correspond to $V_\theta = V\sin\theta = 7\times 10^{-4}$ meV and $F_{100} = 9\times10^6$ Pa. The lower inset displays the theoretically calculated temperature dependence of the spin lifetime $\tau = 1/\lambda_{\min}$, an inverse of the lowest eigenvalue of relaxation operator $\mathcal{L}$, Eq. (10). It is characterized by two activation energies Δ_2 and Δ_3 (the corresponding activation processes are shown in Fig. 1(b) with dashed lines)

ψ'_μ of $H_{\mathbf{q}\nu}$ with phonon wavevector q and polarization ν obeys parity selection rules[14] and can be written in the form

$$\langle\psi_\mu|H_{\mathbf{q}\nu}|\psi_{\mu'}\rangle = \hat{I}\sum_{j=1}^{3} M^j_{\mathbf{q}\nu}[A^+_{j,\mu,\mu'} + q_j r_u A^-_{j,\mu,\mu'}], \tag{2}$$

where $A^{\pm}_{j,\mu,\mu'} = \alpha^\mu_j \alpha^{\mu'}_{\pm j} \pm \alpha^\mu_{-j}\alpha^{\mu'}_{\mp j}$. Here $M^j_{\mathbf{q}\nu}$ is the energy shift of valleys $\mathbf{k}_{\pm j}$ due to the phonon mode $\mathbf{q}$ with polarization ν. In can be expressed in terms of the deformation potential constants and angular functions[14]. A^+ and A^- are zero for the states μ, μ' with the same and opposite parities, respectively. In the latter case the transition amplitude (2) contains a very small quantity $qr_u \sim 10^{-4}$ where $r_u = \int F^2_z(\mathbf{r}) z \sin(\kappa_u z) d\mathbf{r}$ is determined by the overlap in k-space of the envelope functions localized near the different conduction band minima separated by umklapp vector $\kappa_u \simeq 0.3 \times 10^8$ cm^{-1}[14] .

Matrix elements $\langle\psi_\mu|H_{\rm st}|\psi_{\mu'}\rangle = \Xi_u \hat{I}\sum_{j=1}^3 A^+_{j\mu\mu'} u_{jj}$ depend on a shear deformation potential Ξ_u that couples the long-wavelength strain tensor components u_{jj} to the donor states[12]. For most experimental situations the strain is caused by a superposition of an external uniaxial and much weaker random biaxial stress that completely removes the orbital degeneracy. A compressive uniaxial (001) stress F_{001} only partially splits the $1s(E+T_2)$ manifold[9,12] as shown in Fig. 1. The ground state is T_{2z} and the first excited state is a superposition of E_θ and A_1 orbitals with dominant E_θ character. The third level is triple-degenerate, corresponding to states $T_{2x}, T_{2y}, E_\epsilon$ as shown in Fig. 1. For $F_{001} = 9\times10^6$ Pa the splitting of T_{2z} and E_θ levels is $\simeq 0.2$ meV; much larger than the random-stress induced level broadening in ^{28}Si [17,18]. We note that due to the symmetry of an interaction involving deformation potentials[12] an *arbitrary* biaxial stress mixes only even-parity states, A_1, E_θ and E_ϵ and therefore preserves the above parity-selection rules.

Matrix elements of the Zeeman Hamiltonian equal

$$\langle\psi_\mu|H_{\rm B}|\psi_{\mu'}\rangle = \sum_{j=1}^{3} g_\perp \mu_B B_j \hat{S}_j (\delta_{\mu\mu'} + \varepsilon A^+_{j\mu\mu'}), \tag{3}$$

where μ_B is the Bohr magneton, $\hat{S}_j$ and B_j are, respectively, the 3 cartesian components of the electron spin operator and magnetic field. Also $\varepsilon = (g_\parallel - g_\perp)/g_\perp$, and $g_\parallel, g_\perp$ are the components of the g-tensor[12].

There exists a small spin-orbit interaction in the ground state of Li donor induced by the host silicon lattice[12]. It is typically smaller then the strain and Zeeman terms. The spin-orbit Hamiltonian H_{so} reads[12]:

$$\begin{aligned} H_{\text{so}} = & -i\hat{S}_z \left(\lambda'|T_{2z}\rangle\langle E_\varepsilon| + \lambda|T_{2x}\rangle\langle T_{2y}|\right) \\ & -i\hat{S}_x \left(\lambda'|E_+\rangle\langle T_{2x}| + \lambda|T_{2y}\rangle\langle T_{2z}|\right) \\ & -i\hat{S}_y \left(\lambda'|E_-\rangle\langle T_{2y}| + \lambda|T_{2z}\rangle\langle T_{2x}|\right) + \text{ h.c.,} \end{aligned} \tag{4}$$

where $|E_\pm\rangle \equiv \frac{1}{2}\left(|E_\varepsilon\rangle \pm \sqrt{3}|E_\theta\rangle\right)$, and small constants $\lambda \simeq 0.003$ meV and $\lambda' = 0.007$ meV determine the strength of the spin-orbit coupling within the triplet and between the triplet and singlet, respectively[12].

III. CHIRAL SYMMETRY

Spin-orbit Hamiltonian H_{so} mixes the orbital states of opposite parities and, as one might expect, it violates the above parity selection rules for the transition rates. However, we show below that the time-reversal symmetry in the absence of a magnetic field leads to a factorization of the total Hamiltonian and emergence of the new selection rules that persist for finite magnetic fields of certain orientations. We assume that the magnetic field $\mathbf{B} = B\hat{z}$. Then the eigenstates of the Hamiltonian $H^{(0)}$ form two non-overlapping subspaces with an element in each subspace being a linear superposition of the following 6 basis vectors $|\chi_\sigma\rangle|\psi_\mu\rangle$:

$$\begin{aligned} |\Phi_\sigma^{(0)}\rangle \; = & \; |\chi_\sigma\rangle \left(c_z|T_{2z}\rangle + c_\theta|E_\theta\rangle + c_\varepsilon|E_\varepsilon\rangle + c_{A_1}|A_1\rangle\right) \\ + & \; |\chi_{-\sigma}\rangle \left(c_x|T_{2x}\rangle + c_y|T_{2y}\rangle\right), \quad \sigma = \pm 1, \end{aligned} \tag{5}$$

where $\hat{\sigma}_z|\chi_\sigma\rangle = \sigma|\chi_\sigma\rangle$, $\hat{\sigma}_z$ is the Pauli matrix, and σ is a subspace index. The eignstates $|\Phi_+^{(0)}\rangle$ and their time-reversed counterparts $|\Phi_-^{(0)}\rangle$ are also the eigenstates of the "chirality" operator $\hat{Z} = \hat{R}_z(\pi)\hat{\sigma}_z$, where $\hat{R}_z(\pi)$ is the operator of rotation through the angle π around z-axis. Indeed, the operator $\hat{Z}$ commutes with the Hamiltonian $H^{(0)}$ and $\hat{Z}|\Phi_\pm^{(0)}\rangle = \pm|\Phi_\pm^{(0)}\rangle$. In the absence of the magnetic field pairs of similar eigenstates with opposite chiralities form Kramers doublets with the same energy. A finite magnetic field B lifts the Kramers degeneracy. However for H_B with $\mathbf{B} = B\hat{z}$ the chirality still remains a good quantum number and the subspaces do not mix despite an arbitrary biaxial strain present in $H^{(0)}$. Similar subspaces can be constructed for $\mathbf{B} = B\hat{x}$ and $\mathbf{B} = B\hat{y}$.

Watkins and Ham postulated a small displacement $\mathbf{d}$ of the Li atom from a tetrahedral interstitial site[12], preferentially in the direction of the uniaxial stress $\mathbf{F} \parallel \mathbf{d}$ to generate the correct number of lines in the Si:Li ESR spectrum. It gives rise to a short-range electric dipole potential H_d (1) with the strength V and matrix elements

$$\langle \psi_\mu | H_\mathrm{d} | \psi_{\mu'} \rangle = 2iV\hat{I} \sum_{j=1}^{3} A^{-}_{j,\mu,\mu'} d_j/d, \quad d_j = \mathbf{d} \cdot \hat{x}_j, \tag{6}$$

connecting states of opposite parities and the same spin orientation. Using (5), (6) and coefficients α^μ_j one gets

$$\langle \Phi^{(0)}_\sigma | H | \Phi^{(0)}_{-\sigma} \rangle = 0 \quad \text{for} \quad \mathbf{B} \parallel \mathbf{d} \parallel \hat{x}_j, \tag{7}$$

where $\hat{x}_j = \hat{z}$, $\hat{y}$ or $\hat{x}$. However, we will assume a small random misalignment, $|\hat{x}_j \times \mathbf{d}/d| = |\sin\theta| \ll 1$ (perhaps, due to a random biaxial stress in addition to a strong uniaxial stress $\mathbf{F}{=}F\hat{x}_j$). It will lead to a slight mixing of the "left" and "right" states $\langle \Phi^{(0)}_\sigma | H | \Phi^{(0)}_{-\sigma} \rangle \propto V_\theta \equiv V\sin\theta$.

IV. TRANSITION RATES

Consider $\mathbf{B} \| \mathbf{F} \| \hat{x}_j$ ($\hat{x}_j = \hat{z}, \hat{y}\,\mathrm{or}\,\hat{x}$). Then the matrix elements of $H_{q\nu}$ between a pair of exact eigenstates, $H\Phi_n = \mathcal{E}_n\Phi_n$, that are predominantly "left" and "right" have the form: $\langle \Phi_n | H_{\mathbf{q}\nu} | \Phi_m \rangle \simeq C^\mathrm{u}_{\mathbf{q}\nu} q r_u + C^\mathrm{d}_{\mathbf{q}\nu} \frac{V_\theta}{\mathcal{E}_n - \mathcal{E}_m}$. The first term is due to an umklapp process ($qr_u{\sim}10^{-4}$) and the second term is due to a small misalignment $V_\theta{=}V\sin\theta$ of $\mathbf{d}$ and $\hat{x}_j$. Both terms are small and acoustic phonon transitions between the states of opposite chiralities are suppressed. As shown below, under the appropriate conditions each of the chiral subspaces can be made nearly "decoherence free".

An important application of the above rule is a suppression of the spin-flip transitions between the states with dominant characters $|\chi_{\pm 1}\rangle \otimes |\psi_\mu\rangle$ that differ only in spin orientation. Those states always have opposite chiralities We shall label each eigenstates after its dominant character and consider $\mathbf{B} = B\hat{z}$, $\mathbf{F} = F_{001}\hat{z}$. If the compressive stress F_{001} is sufficiently large the Zeeman splitting $g_\perp \mu_B B$ becomes smaller than a stress-induced splitting between E_θ and $E_{T_{2z}}$ (see Fig. 2). Then at low temperature the state $|T_{2z}\uparrow\rangle$ decays directly into the state $|T_{2z}\downarrow\rangle$ of the opposite chirality. There is a competition between umklapp and dipole-induced processes. For moderate uniaxial stress and magnetic field the dipole contribution

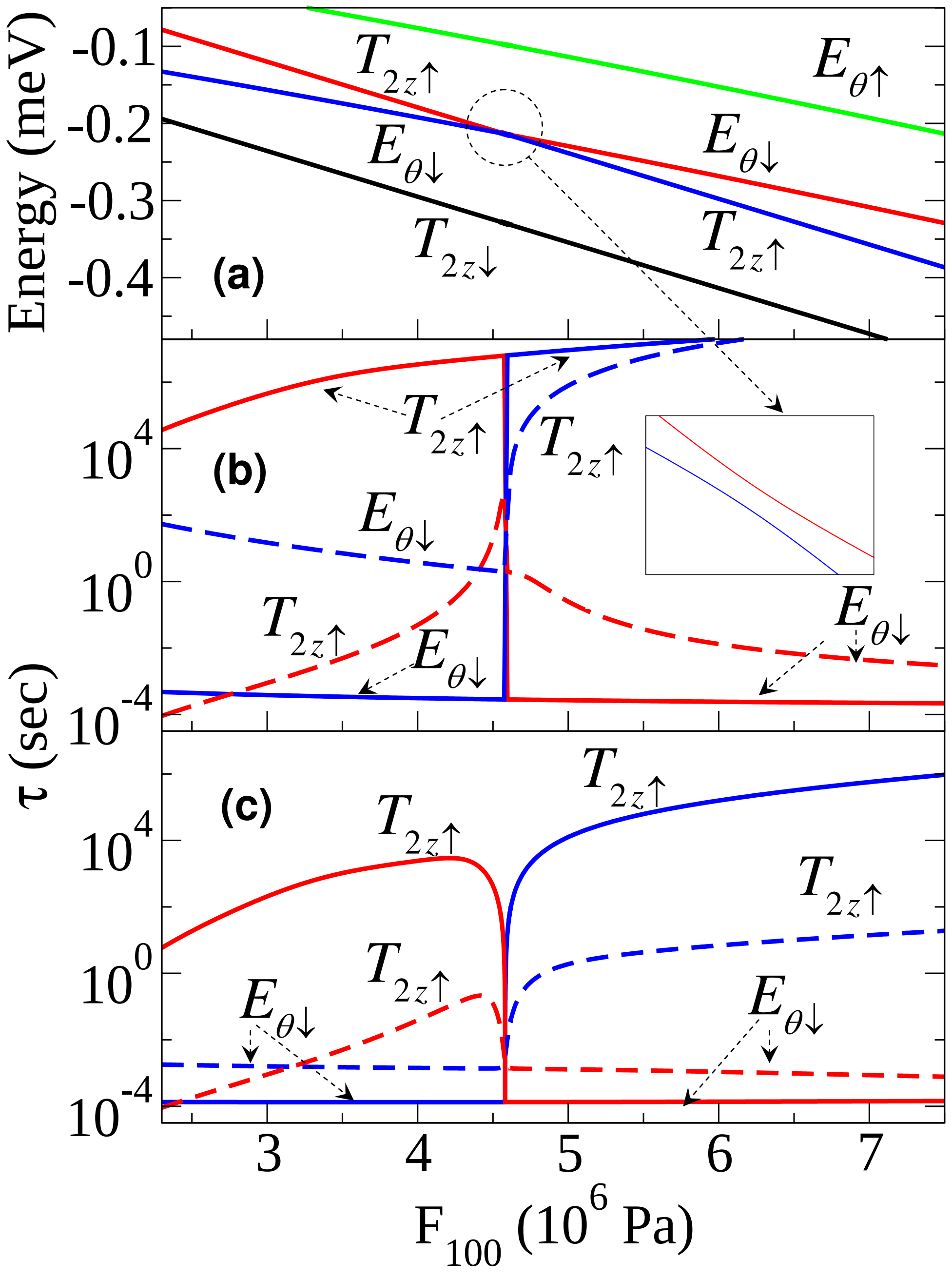

FIG. 2: (Color online.) (a) Calculation of the first four energy levels of Si:Li donor in a magnetic field $B = 1$ T; (b) calculation of the lifetimes of the first two excited states versus compressive 001 stress at T=0.1 K, $B = 1$ T, and $V_\theta = V \sin\theta = 0$. Solid lines — $\mathbf{B} \parallel \hat{z}$ and dashed lines — $\mathbf{B} \parallel \hat{x}$. Inset shows magnified region of the avoided crossing for the magnetic field $\mathbf{B} \perp \hat{z}$; (c) calculation of the lifetimes of the first two excited states versus compressive 001 stress at T=0.1 K, $B = 1$ T, and $V_\theta = V \sin\theta = 4.8 \times 10^{-4}$ meV. Solid lines — $\mathbf{B} \parallel \hat{z}$ and dashed lines — $\mathbf{B} \parallel \hat{x}$.

to the lifetime $\tau_{\mathrm{T}_{2z\uparrow}}$ dominates

$$\tau_{\mathrm{T}_{2z\uparrow}}^{-1} \simeq \tau_{A_1}^{-1} \left(\frac{\lambda\lambda' V_d \sin\theta_d}{\Delta_0^3} \right)^2 \frac{41\upsilon^3}{x^8} \left(\left(\frac{x}{3} \right)^3 + \upsilon^2 \right). \tag{8}$$

Here $\upsilon = g_\perp \mu_B B/\Delta_0$ and $x = \Xi_u(S_{12} - S_{11})F_{001}/6\Delta_0$ where S_{11}, S_{12} are elastic compliance moduli. Prefactor in (8) corresponds to the lifetime $\tau_{A_1} \sim$1 psec of the states A_1 that decay within the same subspaces to E_θ and E_ϵ.

For greater stress and/or magnetic field the umklapp process dominates the decay, giving

$$\tau_{\mathrm{T}_{2z\uparrow}}^{-1} = \tau_{A_1}^{-1} \xi_u \left(\frac{\lambda\lambda' \Delta_0 a_\parallel}{\hbar u_\perp} \right)^2 \frac{7\upsilon^5}{3(x^2 - \upsilon^2)^2}.$$

Here $a_\parallel$ is the longitudinal Bohr radius, $u_\perp$ is the transverse sound velocity, and $\xi_u \simeq 5 \cdot 10^{-5}$ depends on the overlap factor r_u given above via $(r_u/2a_\parallel)^2 = \xi_u - \xi_u^{5/6}$.

We calculated transition rates $W_{n\to m}$ between each pair of the 12 eigenstates $|\Phi_n\rangle$ by numerical diagonalization of H (1) and employing the electron-phonon interaction (2). The stress dependence of the lifetimes of the first two excited states of Si:Li donors at low temperatures is shown in Fig. 2 for $\mathbf{B} \parallel \hat{z}$ and $\mathbf{B} \parallel \hat{x}$. These states can be classified as either orbital (predominantly $E_{\theta\downarrow}$) or spin (predominantly $T_{2z\uparrow}$) excitations. If the stress-induced splitting (SIS) is smaller than the Zeeman splitting (ZS) the first and second excited states correspond to the orbital and spin excitations respectively. As soon as SIS overcomes ZS the two states switch their characters.

The orbital and spin excitations have distinctly different stress dependencies of their lifetimes. The lifetime of the orbital exitation is decreasing with the stress increase while the spin excitation behaves quite oppositely. The stress increase leads to a large separation between $E_{\theta\downarrow}$ and $T_{2z\downarrow}$ states. Consequently the probability of $E_{\theta\downarrow} \to T_{2z\downarrow}$ phonon decay grows as the phonon density of states or faster. On the contrary, the stress does not affect the Zeeman doublet $T_{2z\uparrow}$—$T_{2z\downarrow}$ but rather separates it from other states of the manifold making the spin excitation $T_{2z\uparrow}$ more stable. The lifetime decrease of the orbital excitation is more pronounced for an ideal position of the Li-donor, i.e. for $V_\theta = 0$ (see Fig. 2(b)) and for $\mathbf{B} \parallel \hat{x}$. In this case the orbital excitation and the ground state have different chiralities and the former may decay through the umklapp process only. This adds additional stress dependence due to the matrix element of the umklapp process. The magnitude and the stress dependence of $E_{\theta\downarrow}$-lifetime shown in Fig. 2(b) (dashed line) is very similar to our previous result[10]. The dipole term V_θ reduces both the magnitude and the stress dependence of $E_{\theta\downarrow}$-lifetime, which is weakly decreasing with stress near the value of 10^{-4} s (see Fig. 2(c)).

V. EXPERIMENTAL RESULTS AND COMPARISON WITH THEORY

We conducted a pulsed ESR study of the Li donor spin relaxation under stress. An isotopically-enriched ^{28}Si crystal (800 ppm residual ^{29}Si) was ^{7}Li doped by implanting with a variable energy, up to 360 keV, and a total dose $6{\cdot}10^{12}$ of ^{7}Li/cm^{2} followed by a 30 min anneal at 800 ^{0}C to ensure a homogeneous distribution of the lithium. The estimated Li concentration is $\sim 10^{14}$ cm^{-3}. Uniform, (110), in-palne tensile stress was applied to the Si by gluing fused silica slides (1 mm thick) to the two (001) faces with Apiezon N vacuum grease. This "sandwich" was then frozen to liquid helium temperatures. The thermal expansion coefficient of fused silica is substantially smaller than that of silicon in the temperature range 4-300 K[20], and therefore freezing the sandwich results in an uniform in-plane tensile strain, equivalent to the action of a compressive uniaxial stress F_{001} along the (001) axis of the silicon crystal (perpendicular to the faces). The spin resonance experiments were done at X-band (~0.34 T). Under F_{001} the ESR spectrum is a single line as described by Watkins and Ham[12] though our linewidth (8 μT) is considerably narrower than in their natural Si, since inhomogeneous broadening from the ^{29}Si is eliminated in the isotopically enriched ^{28}Si[19]. The electron magnetization decay measured at 2.1 and 4.5 K with a conventional inversion recovery pulse sequence[21] is shown in Fig. 1.

The stress F_{001} in the sandwiched samples was estimated by performing Fourier transform infrared spectroscopy (FTIR) with a Bruker IFS 66v/S spectrometer (resolution, 0.14 cm^{-1}) on a similarly prepared stressed samples of Li-doped natural float zone silicon (a hole with a diameter 3 mm in the silica slides allowed FIR transmission through the stressed sample). The stress-induced splitting 0.202 meV was observed between the $1s(E+T_2) \rightarrow 2p_0(-)$ line at 21.287 meV and $1s(E+T_2) \rightarrow 2p_0$ line at 21.489 meV. Using this splitting we estimate $F_{001} \simeq 9.0 \times 10^{6}$ Pa based on the previous measurements with calibrated stresses[9] and expressions for the stress-induced line shifts[8,9].

To explain the magnetization recovery data in Fig. 1(b) we studied the multilevel kinetics,

$$\dot{\rho}_n = \sum_{m=1}^{12} \mathcal{L}_{nm}\rho_m, \tag{9}$$

where

$$\mathcal{L}_{nm} = W_{m\to n} - \delta_{nm}\sum_{k=1}^{12} W_{n\to k} \tag{10}$$

is a relaxation operator and $\rho_n = \langle\Phi_n|\hat{\rho}|\Phi_n\rangle$ are individual state populations. We used the stress value $F_{100} = 9{\times}10^6$ Pa estimated from the above FTIR experiment. The only unknown parameter in the expressions for the decay rates W_{nm} is V_θ, or rather V_θ^2 . We were able to fit the two experimental time traces at 2.1 K and 4.5 K using $V_\theta = 7 \times 10^{-4}$ meV ($\sim 0.25\lambda$) as shown in Fig. 1. This value corresponds to a statistical average $(\langle V_\theta^2\rangle)^{1/2}$ over all Li donors. We note the multi-exponential character of the decay at 4.5 K. The temperature dependence of the long-time magnetization kinetics is determined by that of the smallest eigenvalue of the relaxation operator $\lambda_{\min}(T)$. The magnetization decay proceeds via thermal activation to rapidly decaying excited states as shown in Fig. 1(b). For $T < 0.1$ K the spin life-time τ saturates at large value consistent with those shown in Fig. 2.

VI. CONCLUSIONS

To conclude, we introduced a new spin-orbital relaxation mechanism for Li donors in Si and predicted theoretically that the longitudinal spin relaxation T_1 time of a Li donor in Si under the uniaxial compressive stress and magnetic field aligned along the $\hat{x}$,$\hat{y}$ or $\hat{z}$ axis can be very large (hours) for $T < 0.3$ K despite the inverted level structure of interstitial Li donor as compared to Group V substitutional donors in silicon. The orbital relaxation time is 0.1 msec at that temperature. By virtue of the chirality selection rules for the electron-phonon interaction, the donor electron spin can decay only via inter-valley umklapp processes or a very weak direct phonon process caused by a small Li off-site displacement misalignment. At higher temperatures T_1 is reduced to a μs range due to thermal population of the lower excited states which in turn promotes fast transitions within the same chiral subspace allowed by the parity-selection rules. We obtained a very close (within few per cent) agreement with pulsed ESR measurements of T_1 times at $T = 2.1$ K (12 μs) and at $T = 4.5$ K (1.5 μs) that corroborates our prediction of extremely long-lived spin states of Li donors in Si at lower temperatures. Since the chiralty is a universal property of the silicon host ur study can be applied to substitutional donors in Si with similar near-degeneracy of the $1s(E{+}T_2)$ coupled to the ground state via stray electric fields and umklapp processes. Our results of the very long Li spin lifetime can also stimulate the analysis of the possibility of Li spin-based QIP applications with direct long-range elastic-dipole interaction between the Li donor spins similar to that considered in[10,11].

VII. ACKNOWLEDGMENTS

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[*] Electronic address: Vadim.N.Smelyanskiy@nasa.gov
[†] Electronic address: Andre.Petukhov@sdsmt.edu

[1] D. Loss, D.P. DiVincenzo, Phys. Rev. A **57**, 120 (1998).
[2] B.E. Kane, Nature **393**, 133 (1998).
[3] R. Vrijen, et al., Phys. Rev. A **62**, 012306 (2000).
[4] M. Friesen, et al., Phys. Rev. B **67**, 121301 (2003).
[5] J.R. Petta, et al., Science **309**, 2180 (1985).
[6] J.P. Gordon, K.D. Bowers, Phys. Rev. Lett. **1**, 368 (1958).
[7] A.M. Tyryshkin, et al., Phys. Rev. B **68**, 193207 (2003).
[8] R.L. Aggarwal, et al., Phys. Rev. **138**, A 882 (1965).
[9] C. Jagannath, A. Ramdas, Phys. Rev. B **23**, 4426 (1981).
[10] V.N. Smelyanskiy, A.G. Petukhov and V.V. Osipov, Phys. Rev. B **72**, R081304 (2005).
[11] B. Golding and M.I. Dykman, cond-mat/0309147.
[12] G.D. Watkins, F.S. Ham, Phys. Rev. B **1**, 4071 (1970).
[13] G. Feher, Phys. Rev. **114**, 1219 (1959).
[14] T.G. Castner, Phys. Rev. **139**, 58 (1963); Phys. Rev. Lett. **8**, 13 (1962); Phys. Rev. **155**, 816 (1967).
[15] H. Hasegawa, Phys. Rev. **118**, 1523 (1960).
[16] L.M. Roth, Phys. Rev. **118**, 1534 (1960).
[17] A. Yang, et al., Physica B **376-377**, 54 (2006).
[18] D. Karaiskaj, et al., Phys. Rev. Lett. **90**, 186402 (2003).
[19] Li line is ∼100 times stronger than Li_2O line.
[20] A. Nyilas, AIP Conf. Proc. **711**, 151 (2004).
[21] A. Schweiger and G. Jeschke, *Principles of Pulse Electron Paramagnetic Resonance* (Oxford University Press, Oxford, 2001).